Liquid Crystal Display and Backlight Integrated Controller

The MC34271 is a low power dual switching voltage regulator, specifically designed for handheld and laptop applications, to provide several regulated output voltages using a minimum of external parts. Two uncommitted switching regulators feature a very low standby bias current of 5.0 μA , and an operating current of 7.0 mA capable of supplying output currents in excess of 200 mA.

Both devices have three additional features. The first is an ELD Output that can be used to drive a backlight or a liquid crystal display. The ELD output frequency is the clock divided by 256. The second feature allows four additional output bias voltages, in specific proportions to V_B , one of the switching regulated output voltages. It allows use of mixed logic circuitry and provides a voltage bias for N–Channel load control MOSFETs $^{\text{IM}}$. The third feature is an Enable input that allows a logic level signal to turn—"off" or turn—"on" both switching regulators.

Due to the low bias current specifications, this device is ideally suited for battery powered computer, consumer, and industrial equipment where an extension of useful battery life is desirable.

MC34271 Features:

- Low Standby Bias Current of 5.0 μA
- Uncommitted Switching Regulators Allow Both Positive and Negative Supply Voltages
- Logic Enable Allows Microprocessor Control of All Outputs
- Synchronizable to External Clock
- Mode Commandable for ELD and LCD Interface
- Frequency Synchronizable
- Auxiliary Output Bias Voltages Enable Load Control via N-Channel FETs

MAXIMUM RATINGS (T_A = 25°C, unless otherwise noted.)

Rating	Symbol	Value	Unit
Input Voltage	V _{DD}	16	Vdc
Power Dissipation and Thermal Characteristics			
Maximum Power Dissipation – Case 873	PD	1.43	W
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	100	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	60	°C/W
Output #1 and #2 Switch Current	I _{SL} & I _{SB}	500	mA
Output #1 and #2 "Off"-State Voltage	V _{SL}	60	Vdc
Feedback Enable MOSFETs "Off"-State Voltage	VLF	20	Vdc
Operating Junction Temperature	TJ	125	°C
Operating Ambient Temperature	T _A	0 to +70	°C
Storage Temperature Range	T _{stg}	-55 to +150	°C

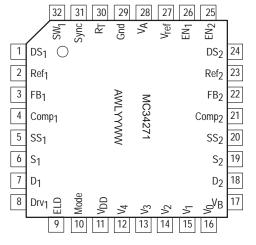


http://onsemi.com



QFP-32 FB SUFFIX CASE 873

PIN CONNECTIONS AND MARKING DIAGRAM



(Top View)

A = Assembly Location

WL = Wafer Lot

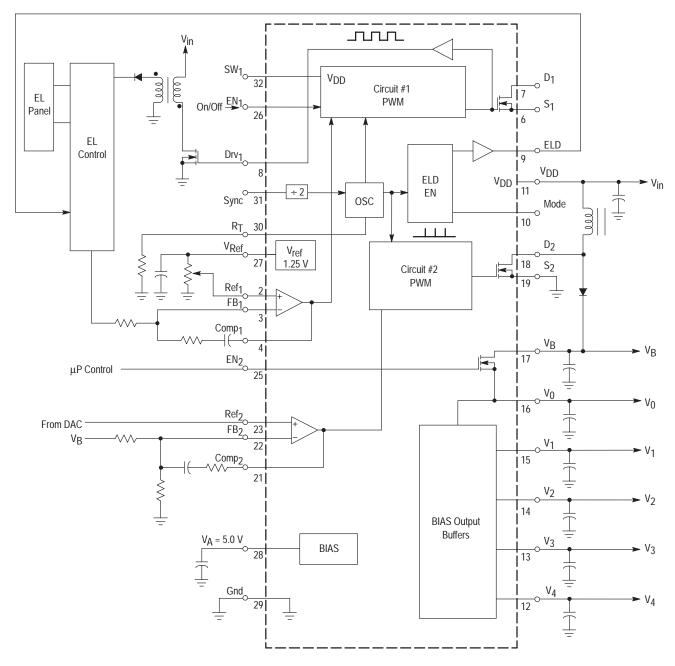
YY = Year

WW = Work Week

ORDERING INFORMATION

Device	Package	Shipping
MC34271FB	QFP-32	250 Units / Tray

Representative Block Diagram



This device contains 350 active transistors.

ELECTRICAL CHARACTERISTICS ($V_{DD} = 6.0 \text{ V}$, for typical values $T_A = \text{Low to High [Note 1]}$, for min/max values T_A is the operating ambient temperature range that applies, unless otherwise noted.)

Characteristic	Symbol	Min	Тур	Max	Unit
REFERENCE SECTION	•				•
Reference Voltage (T _J = 25°C)	V _{ref}	1.225	1.250	1.275	V
Line Regulation (V _{DD} = 5.0 V to 12.5 V)	Reg _{line}	_	2.0	10	mV
Load Regulation (I _O = 0 to 120 μA)	Reg _{load}	_	2.0	10	mV
Total Variation (Line, Load and Temperature)	V _{ref}	1.215	_	1.285	V
ERROR AMPLIFIERS	•			'	•
Input Offset Voltage (V _{CM} = 1.25 V)	VIO	_	1.0	10	mV
Input Bias Current (V _{CM} = 1.25 V)	I _{IB}	_	120	600	nA
Open Loop Voltage Gain (V _{CM} = 1.25 V, V _{COMP} = 2.0 V)	AVOL	80	100	-	dB
Output Voltage Swing High State (I_{OH} = -100 μ A) Low State (I_{OL} = 100 μ A)	VeOL VeOL	V _A -1.5	4.0 -	5.5 1.0	V
BIAS VOLTAGE					
Voltage ($V_{DD} = 5.0 \text{ V}$ to 12.5 V, $I_{O} = 0$)	VA	4.6	5.0	5.4	V
OSCILLATOR AND PWM SECTIONS					
Total Frequency Variation Over Line and Temperature $V_{DD} = 5.0 \text{ V}$ to 10 V, $T_A = 0^{\circ}$ to 70°C, $R_T = 169 \text{ k}$	fosc	90	115	140	kHz
Duty Cycle at Each Output Maximum Minimum	DC _{max} DC _{min}	92 -	95 -	_ 0	%
Sync Input Input Resistance (V _{Sync} = 3.5 V) Minimum Sync Pulse Width	R _{sync} T _p	25 -	50 1.0	100 –	kΩ μs
OUTPUT MOSFETs					1
Output Voltage – "On"–State (I _{sink} = 200 mA)	VOL	-	150	250	mV
Output Current – "Off"–State (V _{OH} = 40 V)	ІОН	-	0.1	1.0	μΑ
Rise and Fall Times	t _r , t _f	_	50	_	ns
EL DISCHARGE OUTPUT (ELD) AND DRV ₁					
Output Voltage – "On"–State (I _{Sink} = 100 μA)	VOL	_	30	100	mV
Output Voltage – "On"–State (I _{Sink} = 50 mA)	VOL	_	2.0	2.5	V
Output Voltage – "Off"–State ($I_{Source} = -100 \mu A$)	Voн	V _{DD} -0.5	5.9	_	V
Output Voltage – "Off"-State (I _{Source} = -50 mA)	VOH	V _{DD} -3.5	3.3	_	V
FEEDBACK ENABLE SWITCHES (DS ₁ , DS ₂)					
Output Voltage – "Low"–State (I _{sink} = 1.0 mA)	VfeOL	_	10	100	mV
Output Current – "Off"–State (V _{OH} = 12.5 V)	IfeOH	_	0.6	1.0	μΑ
SWITCHED V _{DD} OUTPUT (SW ₁)					
Output Voltage Switch "On" (EN ₁ = 1, I_{Source} = 100 μ A) Switch "Off" (EN ₁ = 0, I_{Sink} = 100 μ A)	Vsw _{OH} Vsw _{OL}	5.5 0	5.9 0.1	6.0 0.2	V
AUXILIARY VOLTAGE OUTPUTS					1
V_0 Enable Switch "On"–Resistance: V_B to V_0 "Off"–State Leakage Current ($V_B = 10 \text{ V}$) V_0 Voltage ($V_B = 30 \text{ V}$, $I_{source} = 0 \text{ mA}$) V_0 Resistance ($I_{source} = 4.0 \text{ mA}$)	Rds Ilkg V0 R0	0 0 29.5 20	2.0 0.1 29.9 40	10 2.0 30 60	Ω μΑ V Ω

NOTE: 1. Low duty pulse techniques are used during test to maintain junction temperature as close to ambient as possible.

ELECTRICAL CHARACTERISTICS (continued) ($V_{DD} = 6.0 \text{ V}$, for typical values $T_A = \text{Low to High [Note 1]}$, for min/max values T_A is the operating ambient temperature range that applies, unless otherwise noted.)

Characteristic		Symbol	Min	Тур	Max	Unit
AUXILIARY VOLTAGE OUTPUTS		•	•			
V ₁ , V ₂ , V ₃ , V ₄ Outputs 1–V ₁ /V ₀ Ratio 1–V ₂ /V ₀ Ratio V ₃ /V ₀ Ratio V ₄ /V ₀ Ratio		D	0.0500 0.1010 0.1010 0.0500	0.0520 0.1035 0.1035 0.0520	0.0535 0.1065 0.1065 0.0535 60	0
Output Resistance (I _{Source} = 4.0 mA) Output Short Circuit Current		R _o I _{ss}	20 5.0	40 10	20	Ω mA
LOGIC INPUTS (EN ₁ , EN ₂ , MODE)		1 00	1		1	
Input Low State		VIL	0	_	0.8	V
Input High State		VIH	2.0	-	6.0	V
Input Impedance		R _{in}	25	50	100	kΩ
SOFT START CONTROL (SS ₁ ,SS ₂)						
Charge Current (Capacitor Voltage = 1.0 V to	4.0 V)	I _{chg}	0.5	1.0	2.5	μΑ
Discharge Current (Capacitor Voltage = 1.0 V	/)	I _{dschg}	250	650	-	μΑ
TOTAL SUPPLY CURRENT						
V _{DD} Current Standby Mode (EN ₁ = EN ₂ = 0)	$V_{DD} = 6.0 \text{ V}$ $V_{DD} = 16 \text{ V}$	lcc		2.0 3.0	5.0 15	μΑ
V _{DD} Current Backlight "On" (EN ₁ = 1; EN ₂ = 0)		lcc	-	0.7	3.0	mA
V _{DD} Current LCD "On" (No Inductor) (EN ₁ = 0; EN ₂ = 1)		lcc	-	0.9	2.0	mA
V _B Current (V ₀ = 35 V)		Io	T -	1.2	3.0	mA

NOTE: 1. Low duty pulse techniques are used during test to maintain junction temperature as close to ambient as possible.

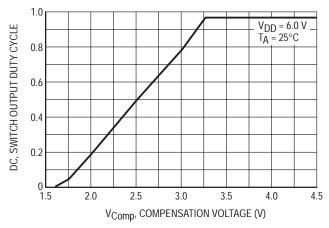


Figure 1. Switch Output Duty Cycle versus Compensation Voltage

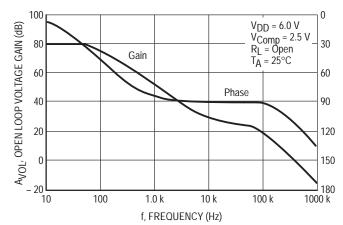


Figure 2. Error Amp Open Loop Gain and Phase versus Frequency

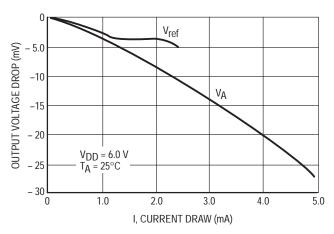


Figure 3. Reference Voltage Change versus Reference Current

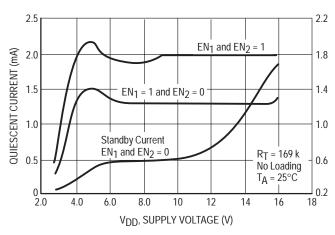


Figure 4. Quiescent Current versus Supply Voltage

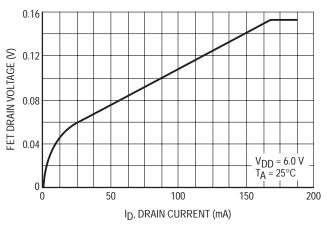


Figure 5. FET Drain Voltage versus Sink Current

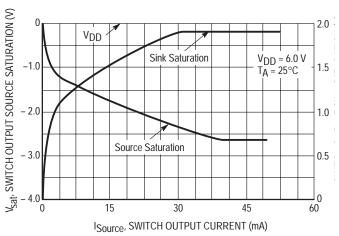


Figure 6. ELD and DRV₁ Switch Output Source and Sink Saturation versus Current

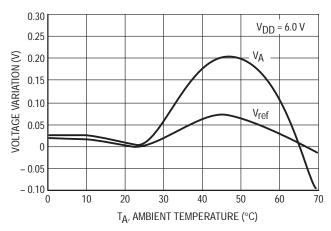


Figure 7. V_{ref} and V_A Variation versus Temperature

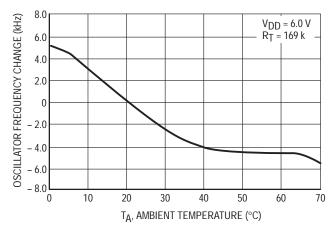
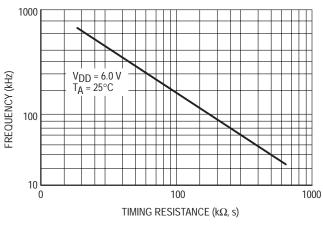


Figure 8. Oscillator Frequency Variation versus Temperature





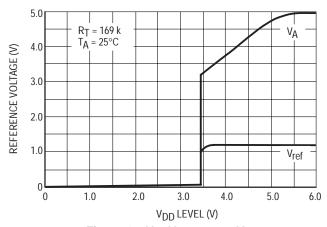


Figure 10. VA, Vref versus VDD

OPERATING DESCRIPTION

The MC34271 is a monolithic, fixed frequency power switching regulator specifically designed for dc to dc converter and battery powered applications. This device operates as a fixed frequency, voltage mode regulator containing all the active functions required to directly implement step—up, step—down and voltage inverting converters with a minimum number of external components. Potential markets include battery powered, handheld, automotive, computer, industrial and cost sensitive consumer products. A description of each section is given below with the representative block diagram shown in Figure 11.

Oscillator

The oscillator frequency is programmed by resistor RT. The charge to discharge ratio is controlled to yield a 95% maximum duty cycle at the switch outputs. During the fall time of the internal sawtooth waveform, the oscillator generates an internal blanking pulse that holds the inverting input of the AND gates high, disabling the output switching MOSFETs. The internal sawtooth waveform has a nominal peak voltage of 3.3 V and a valley voltage of 1.7 V.

Pulse Width Modulators

Both pulse width modulators consist of a comparator with the oscillator ramp voltage applied to the noninverting input, while the error amplifier output is applied to the inverting input. A third input to the comparator has a 0.5 mA typical current source that can be used to implement soft start. Output switch conduction is initiated when the ramp waveform is discharged to the valley voltage. As the ramp voltage increases to a voltage that exceeds the error amplifier output, the latch resets, terminating output MOSFET conduction for the duration of the oscillator ramp. This PWM/latch combination prevents multiple output pulses during a given oscillator cycle.

Each PWM circuit is enabled by a logic input. When disabled, the entire block is turned off, drawing only leakage current from the power source. Shared circuits, like the

reference and oscillator, can be activated by either EN_1 or EN_2 .

Circuit #1 has an ELD output which may be used to drive an LCD or backlight. Its output frequency is the oscillator frequency divided by 1024.

Error Amplifiers and Reference

Each error amplifier is provided with access to both inverting and noninverting inputs, and the output. The Error Amplifiers' Common Mode Input Range is 0 to 2.5 V. The amplifiers have a minimum dc voltage gain of 60 dB. The 1.25~V reference has an accuracy of $\pm 4.0\%$ at room temperature.

External loop compensation is required for converter stability. A simple low–pass filter is formed by connecting a resistive divider from the output to the error amplifier inverting input, and a series resistor–capacitor from the error amplifier output also to the to the inverting input. The step down converter is easiest to compensate for stability. The step–up and voltage inverting configurations, when operated as continuous conduction boost or flyback converters, are more difficult to compensate, and may require a lower loop design bandwidth.

MOSFET Switch Outputs

The output MOSFETs are designed to switch a maximum of 60 V, with a peak drain current capability of 500 mA. In circuit #1 an additional DRV₁ output is provided for interfacing with an external MOSFET. The gates of the MOSFETs are held low when the circuit is disabled.

Auxiliary Output Voltages

Output voltages V_0 through V_4 are provided for use as references or bias voltages. V_0 is the circuit #2 output voltage, when an internal FET switch is activated. The other auxiliary output voltages are proportional to V_B . The amplifiers for V_1 and V_2 are powered from V_0 , while the amplifiers for V_3 and V_4 are powered from V_{DD} .

 SW_1 Circuit #1 Bias Supply 32 D_1 DS₁ EL Q "On/Off" Panel EN₁ ÷N ELD 26 V_{DD} 8 Drv₁ V_{DD} V_{DD} ÷2 11 OSC 31 Sync Mode 3 10 30 R_T 169 k $\perp \perp \perp$ D_2 V_{ref} 1.25 V Ŧ Ref₁ <u>-[R</u>Q1 En ⊨ ± Brightness FB₁ V_{DD} Comp₁ **\$**∕ \$ SS₁ Ē V_{DD2} Circuit #2 Bias Supply $^{\textrm{V}_{\textrm{B}}}_{\textrm{6.0}}$ V to 30 V Ref₂ DAC V_{B} 23 FB₂ Comp 21 SS₂ v_0 20 16 DS₂ V_1 V_2 25 EN₂ V_{DD2} LCD Display V_3 BIAS Ī 28 V_{DD2} Gnd V_4

Figure 11. Representative Block Diagram Electroluminescent Backlight Configuration

Figure 12. Auxiliary Supply Configuration

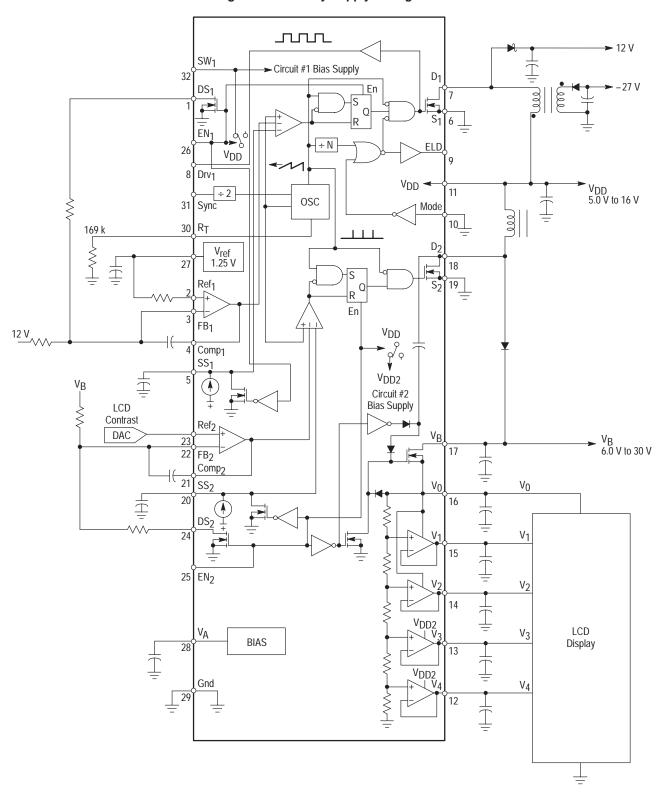
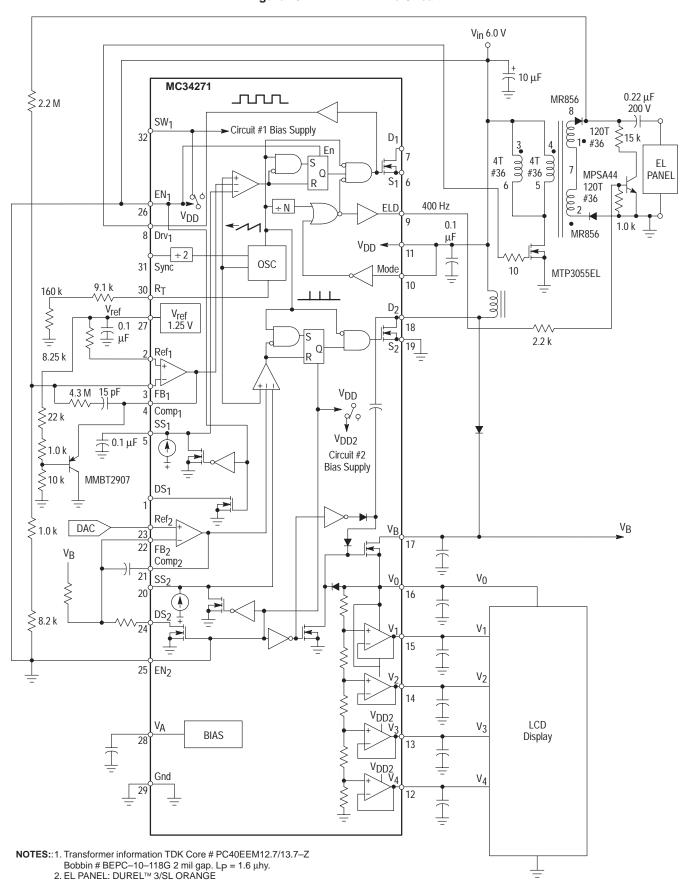
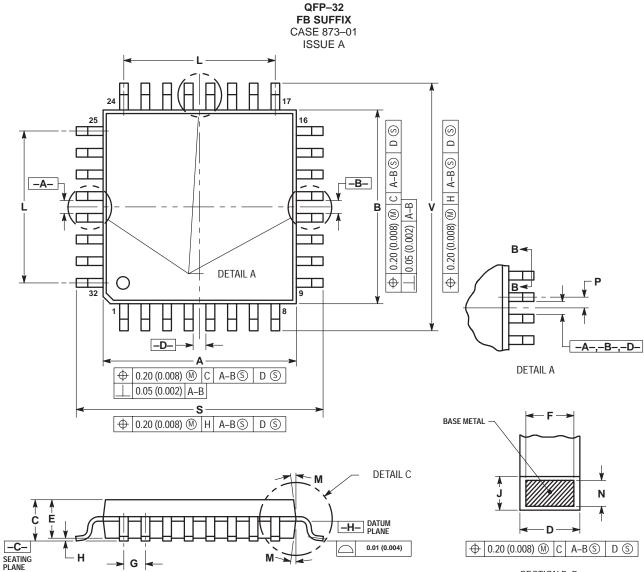


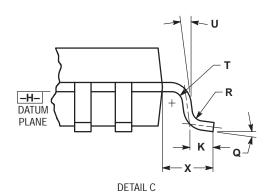
Figure 13. EL PANEL Drive Circuit



PACKAGE DIMENSIONS



SECTION B-B VIEW ROTATED 90° CLOCKWISE



- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- Y14.5M, 1982.

 CONTROLLING DIMENSION: MILLIMETER.

 3. DATUM PLANE -H- IS LOCATED AT BOTTOM OF LEAD AND IS COINCIDENT WITH THE LEAD WHERE THE LEAD EXITS THE PLASTIC BODY AT THE BOTTOM OF THE PARTING LINE.

 4. DATUMS -A-, -B- AND -D- TO BE DETERMINED AT

- 4. DATUMS -A-, -B- AND -D- TO BE DETERMINED A DATUM PLANE -H-.

 5. DIMENSIONS S AND V TO BE DETERMINED AT SEATING PLANE -C-.

 6. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION. ALLOWABLE PROTRUSION IS 0.25 (0.010) PER SIDE. DIMENSIONS A AND B DO INCLUDE MOLD MISMATCH AND ARE DETERMINED
- AT DATUM PLANE -H-.

 7. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

 DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT.

	MILLIM	ETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	6.95	7.10	0.274	0.280	
В	6.95	7.10	0.274	0.280	
С	1.40	1.60	0.055	0.063	
D	0.273	0.373	0.010	0.015	
Ε	1.30	1.50	0.051	0.059	
F	0.273	-	0.010	-	
G	0.80 BSC		0.031 BSC		
Н	-	0.20	-	0.008	
J	0.119	0.197	0.005	0.008	
K	0.33	0.57	0.013	0.022	
L	5.6 REF		0.220 REF		
M	6°	8°	6°	8°	
N	0.119	0.135	0.005	0.005	
Р	0.40 BSC		0.016 BSC		
Q	5°	10°	5°	10°	
R	0.15	0.25	0.006	0.010	
S	8.85	9.15	0.348	0.360	
T	0.15	0.25	0.006	0.010	
U	5°	11°	5°	11°	
V	8.85	9.15	0.348	0.360	
Х	1.0 REF		0.039 REF		

Notes

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affliliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer.

PUBLICATION ORDERING INFORMATION

NORTH AMERICA Literature Fulfillment:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA

Phone: 303–675–2175 or 800–344–3860 Toll Free USA/Canada **Fax**: 303–675–2176 or 800–344–3867 Toll Free USA/Canada

Email: ONlit@hibbertco.com

Fax Response Line: 303-675-2167 or 800-344-3810 Toll Free USA/Canada

N. American Technical Support: 800-282-9855 Toll Free USA/Canada

EUROPE: LDC for ON Semiconductor - European Support

German Phone: (+1) 303–308–7140 (M–F 1:00pm to 5:00pm Munich Time) Email: ONlit–german@hibbertco.com

French Phone: (+1) 303–308–7141 (M–F 1:00pm to 5:00pm Toulouse Time)

Email: ONlit-french@hibbertco.com

English Phone: (+1) 303–308–7142 (M–F 12:00pm to 5:00pm UK Time) Email: ONlit@hibbertco.com

EUROPEAN TOLL-FREE ACCESS*: 00-800-4422-3781

*Available from Germany, France, Italy, England, Ireland

CENTRAL/SOUTH AMERICA:

Spanish Phone: 303–308–7143 (Mon–Fri 8:00am to 5:00pm MST)

Email: ONlit-spanish@hibbertco.com

ASIA/PACIFIC: LDC for ON Semiconductor – Asia Support

Phone: 303–675–2121 (Tue–Fri 9:00am to 1:00pm, Hong Kong Time)

Toll Free from Hong Kong & Singapore:

001-800-4422-3781 Email: ONlit-asia@hibbertco.com

JAPAN: ON Semiconductor, Japan Customer Focus Center 4–32–1 Nishi–Gotanda, Shinagawa–ku, Tokyo, Japan 141–8549

Phone: 81–3–5740–2745 **Email**: r14525@onsemi.com

ON Semiconductor Website: http://onsemi.com

For additional information, please contact your local Sales Representative.